

# NPN SILICON RF POWER TRANSISTOR

## DESCRIPTION:

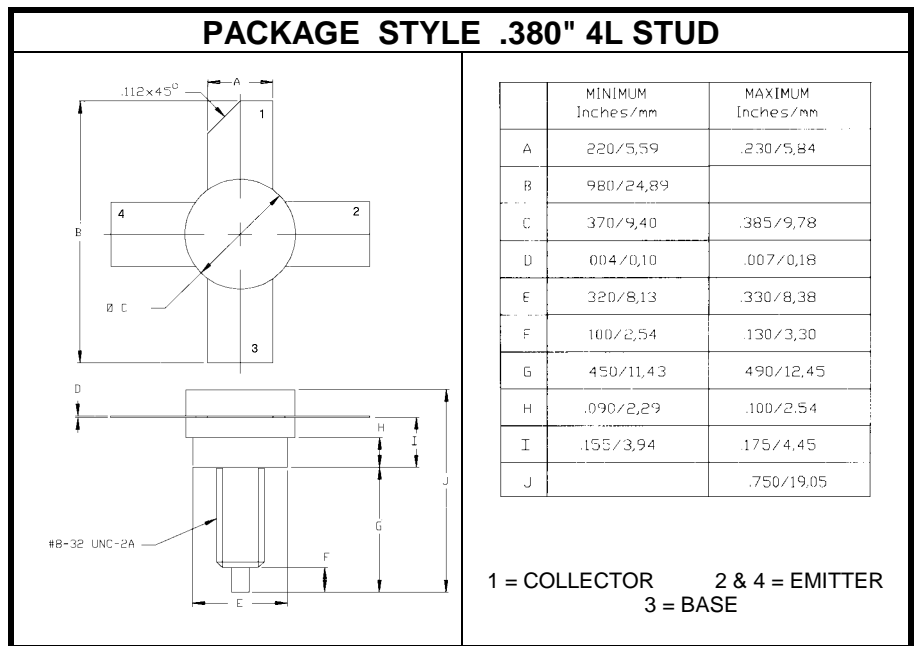
The **ASI BLY91C** is Designed for 28 V Large Signal Class A,B and C Amplifier Applications up to 175 MHz.

## FEATURES INCLUDE:

- Emitter Ballasting
- Gold Metalization
- 3/8" SOE Stud Package

## MAXIMUM RATINGS

<b>I<sub>C</sub></b>	1.0 A
<b>V<sub>CE</sub></b>	35 V
<b>V<sub>CB</sub></b>	65 V
<b>P<sub>DISS</sub></b>	20 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to + 200 °C
<b>T<sub>STG</sub></b>	-65 °C to + 150 °C
<b>θ<sub>JC</sub></b>	8.7 °C/W



## CHARACTERISTICS T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 200 mA	65			<b>V</b>
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 10 mA	35			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 1.0 mA	4.0			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = 36 V			1.0	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 400 mA	10		100	<b>---</b>
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 30 V      f = 1.0 MHz			15	<b>pF</b>
<b>P<sub>G</sub></b>	V <sub>CC</sub> = 28 V      P <sub>OUT</sub> = 8.0 W      f = 175 MHz	12.0	13.0		<b>dB</b>
<b>η<sub>C</sub></b>		65			<b>%</b>